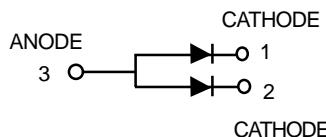
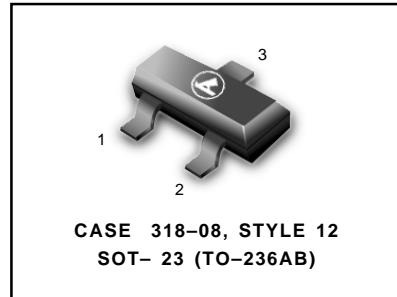


Monolithic Dual Switching Diodes



MMBD2835LT1
MMBD2836LT1



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage MMBD2835LT1	V _R	35	Vdc
		75	
Forward Current	I _F	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board ⁽¹⁾	P _D	225	mW
T _A = 25°C			
Derate above 25°C		1.8	mW/°C
Thermal Resistance, Junction to Ambient	R _{θJA}	556	°C/W
Total Device Dissipation	P _D	300	mW
Alumina Substrate, ⁽²⁾ T _A = 25°C			
Derate above 25°C		2.4	mW/°C
Thermal Resistance, Junction to Ambient	R _{θJA}	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

DEVICE MARKING

MMBD2835LT1 = A3X; MMBD2836LT1=A2X

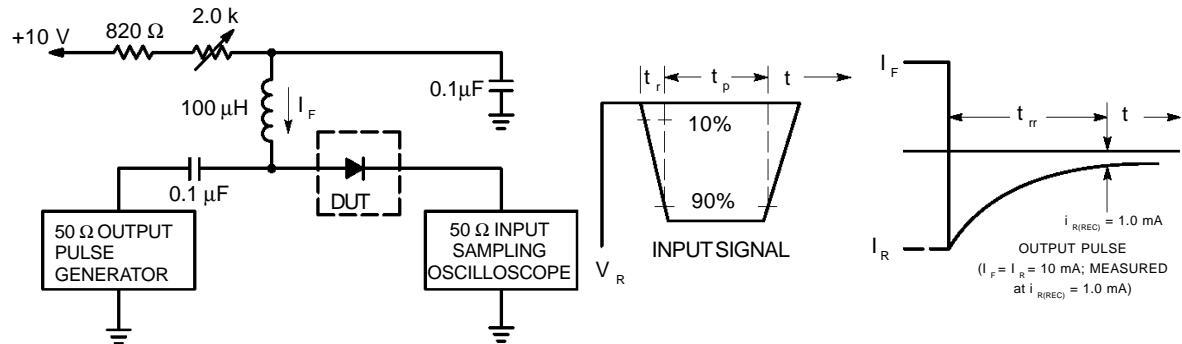
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (EACH DIODE)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Breakdown Voltage(I _R = 100 μAdc)	V _(BR)	35	—	Vdc
MMBD2835LT1		75	—	
Reverse Voltage Leakage Current (V _R = 30 Vdc)	I _R	—	100	nAdc
(V _R = 50 Vdc)	MMBD2835LT1	—	100	
Diode Capacitance (V _R = 0, f = 1.0 MHz)	C _T	—	4.0	pF
Forward Voltage(I _F = 10 mAdc) (I _F = 50 mAdc)	V _F	—	1.0	Vdc
(I _F = 100 mAdc)		—	1.0	
—		—	1.2	
Reverse Recovery Time(I _F =I _R =10 mAdc, I _{R(REC)} =1.0mAdc) (Figure 1)	t _{rr}	—	4.0	ns

1. FR-5 = 1.0 x 0.75 x 0.062 in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

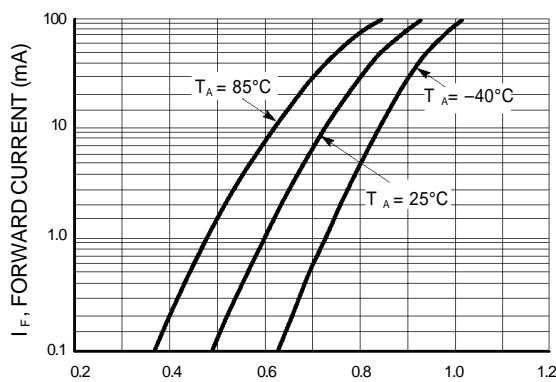
MMBD2835LT1 MMBD2836LT1



Notes: 1. A 2.0 k Ω variable resistor adjusted for a Forward Current (I_F) of 10mA.
 2. Input pulse is adjusted so $I_{R(\text{peak})}$ is equal to 10mA.
 3. $t_p \gg t_{rr}$

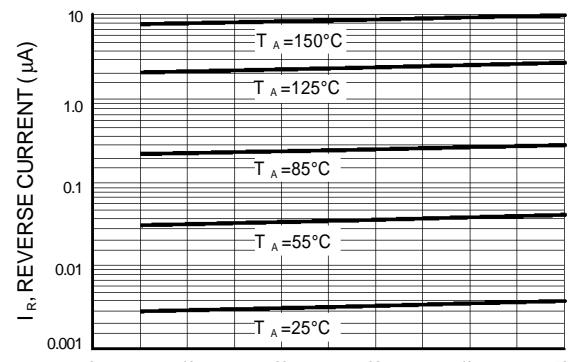
Figure 1. Recovery Time Equivalent Test Circuit

CURVES APPLICABLE TO EACH CATHODE



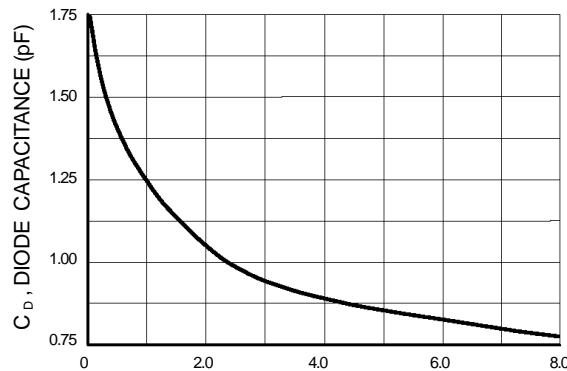
V_F , FORWARD VOLTAGE (VOLTS)

Figure 2. Forward Voltage



V_R , REVERSE VOLTAGE (VOLTS)

Figure 3. Leakage Current



V_R , REVERSE VOLTAGE (VOLTS)

Figure 4. Capacitance